NSN 5962-01-351-7254

Memory Microcircuit - Page 1 of 2



View Online at https://aerobasegroup.com/nsn/5962-01-351-7254

view Offilite at https://aerobasegroup.com/hish/0302-01-031-7204
Body Length:
1.290 inches
Body Width:
Between 0.500 inches and 0.610 inches
Body Height:
Between 0.150 inches and 0.210 inches
Maximum Power Dissipation Rating:
225.0 milliwatts
Operating Tempurature Range:
-55.0/+125.0 degrees celsius
Storage Tempurature Range:
-65.0/+150.0 degrees celsius
End Application:
Satellite communications terminal an/usc-3 (v) 1
Features Provided:
Hermetically sealed and burn in and monolithic and programmed and electrostatic sensitive and erasable and radiation hardened
Inclosure Material:
Ceramic
Inclosure Configuration:
Dual-in-line
Output Logic Form:
N-type metal oxide-semiconductor logic
Input Circuit Pattern:
22 input
Criticality Code Justification:
Feat
Case Outline Source And Designator:
D-3 mil-m-38510
Current Rating Per Characteristic:
45.00 milliamperes reverse current, dc absolute
Terminal Surface Treatment:
Solder
Voltage Rating And Type Per Characteristic:
-0.6 volts input and 6.25 volts input
Time Rating Per Chacteristic:
250.00 nanoseconds delay
Memory Device Type:
Eeprom
Special Features:

Test Data Document:

Nuclear hardness critical item

96906-mil-std-883 standard (includes industry or association standards, individual manufactureer standards, etc.).

NSN 5962-01-351-7254

Memory Microcircuit - Page 2 of 2



Terminal Type Ar	nd Quantity:
------------------	--------------

24 printed circuit

Shelf Life:

N/a

Unit Of Measure:

--

Demilitarization:

Yes - demil/mli

Fiig:

A458a0